

This cross-sectional view shows a curved layer 200 with a radius of curvature $R < 2\mu\text{m}$. A hatched region 220 is located within the curve, and a specific point or feature is labeled 222. Below the curved layer is a patterned layer 78, which includes a central rectangular feature 88. This patterned layer 78 is situated on a substrate 70. Below the substrate 70, there are additional layers or regions labeled 30, 10, and 68.

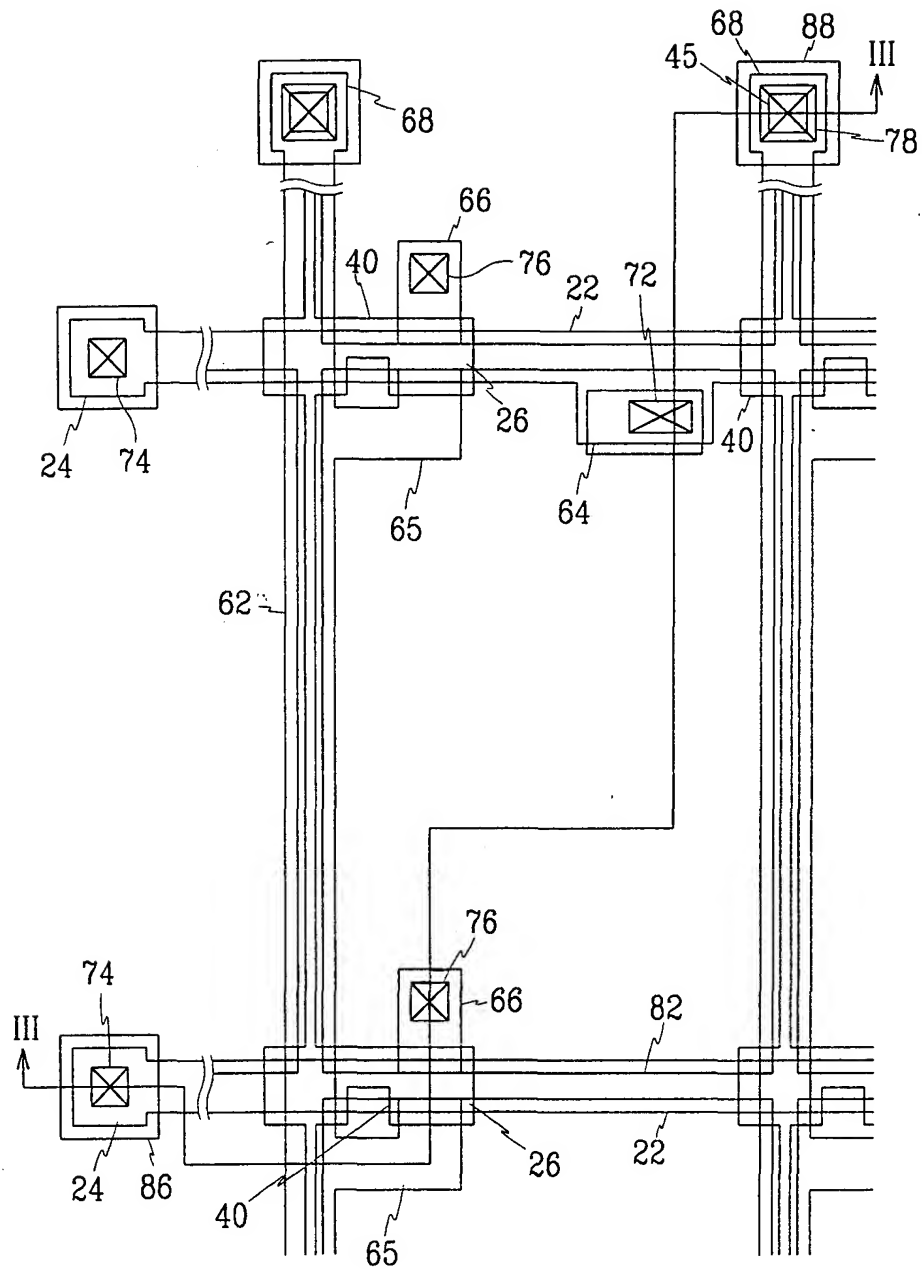


FIG. 3

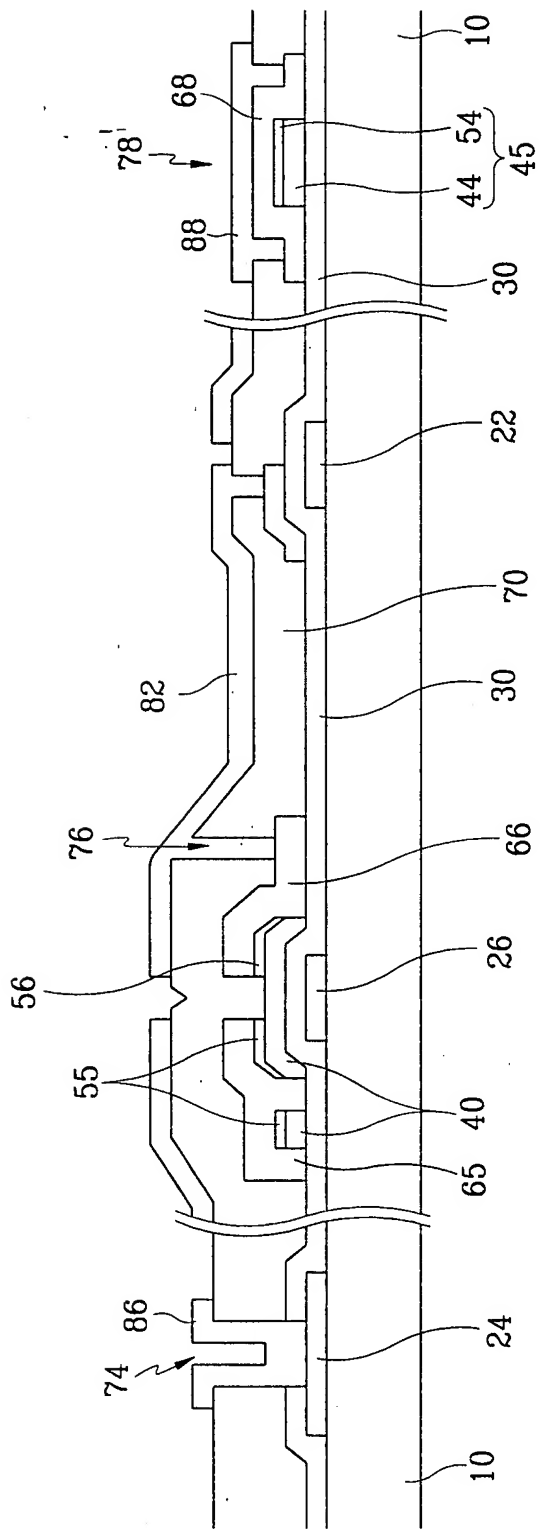


FIG. 4

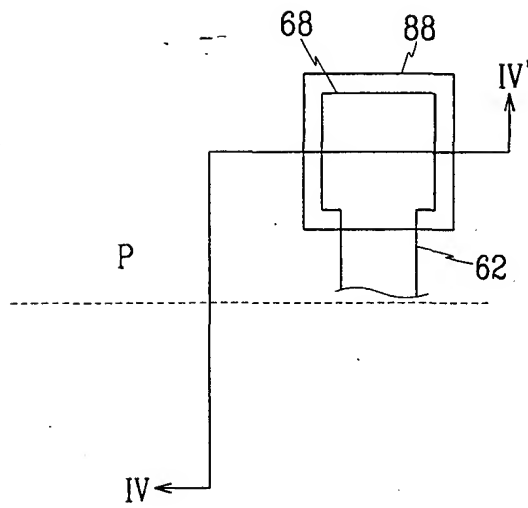


FIG. 5

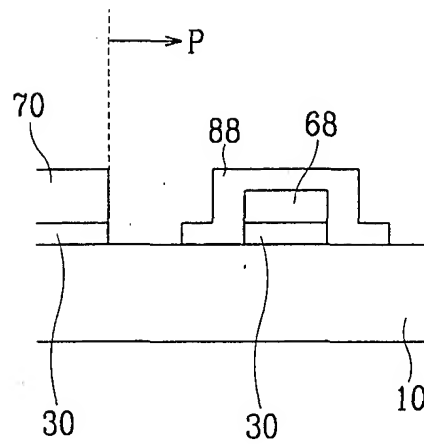


FIG. 6

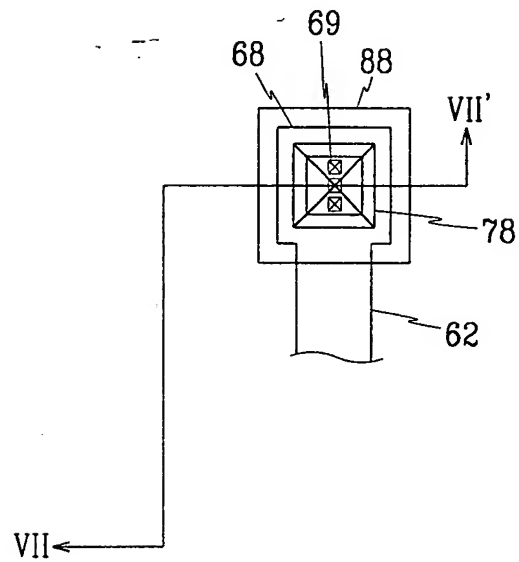


FIG. 7

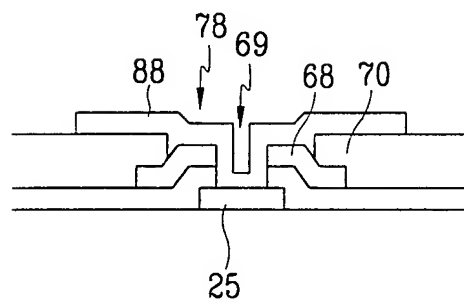


FIG. 8A

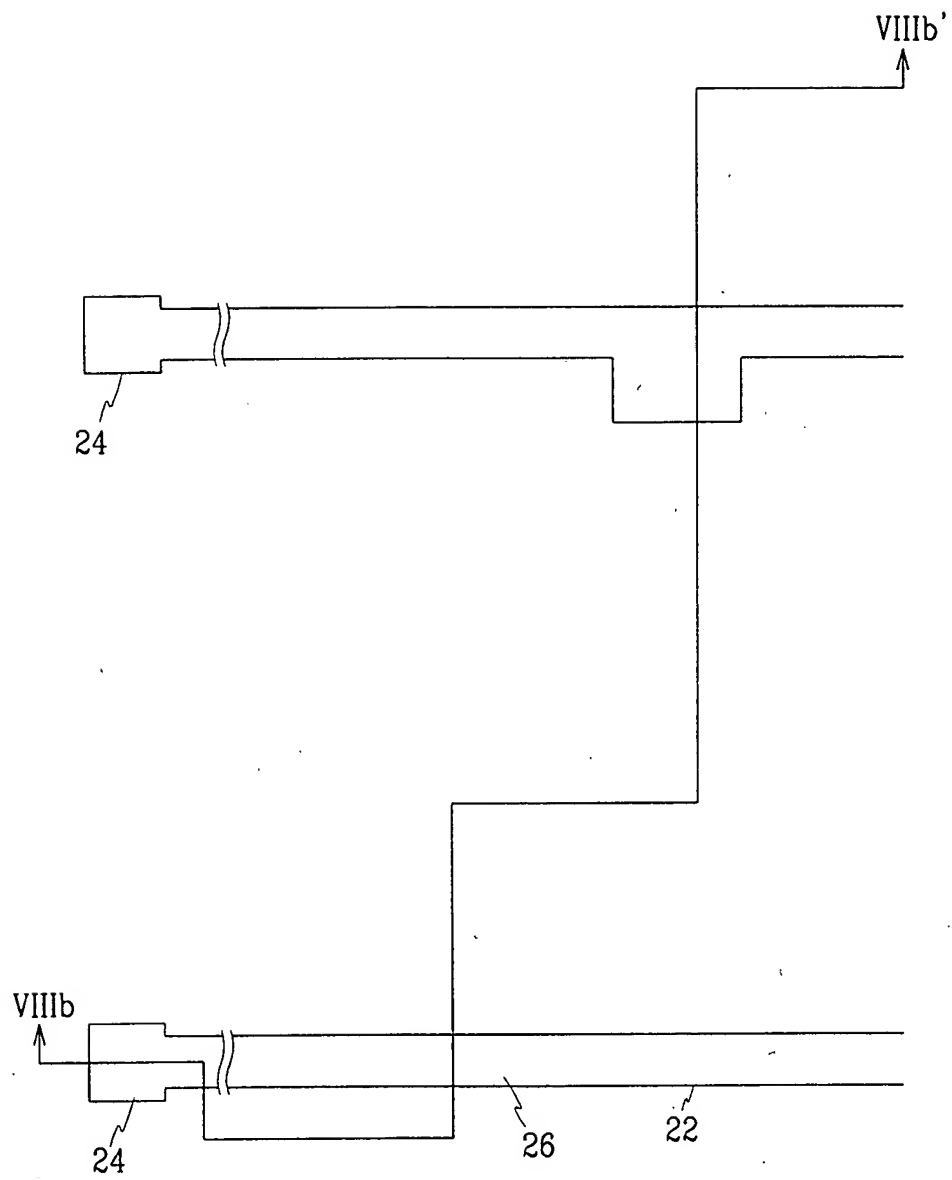


FIG. 8B

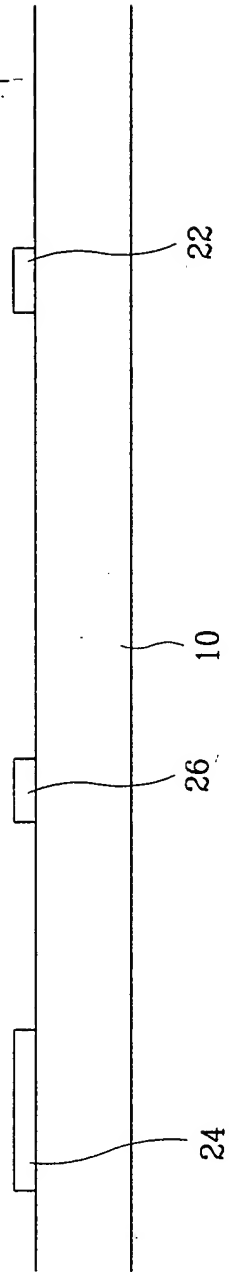


FIG. 9A

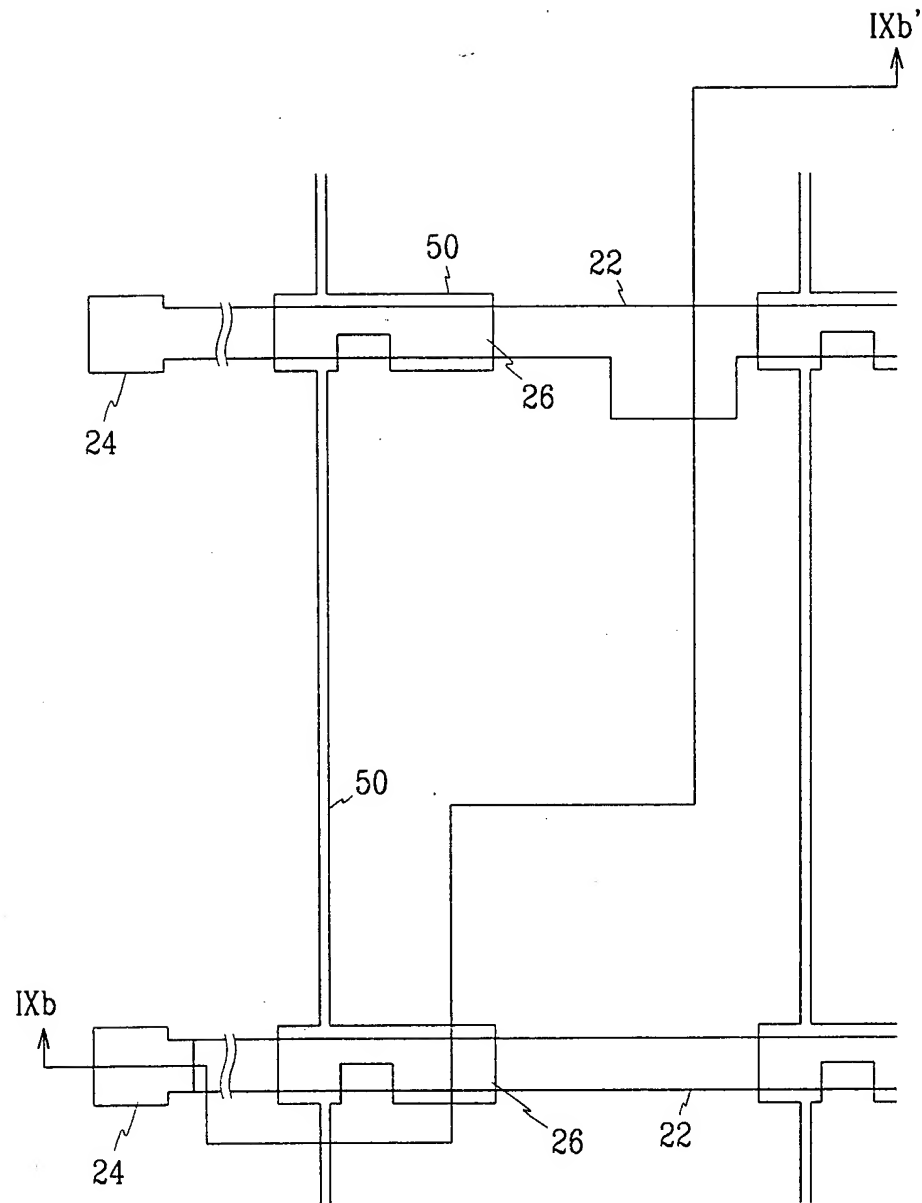


FIG. 9B

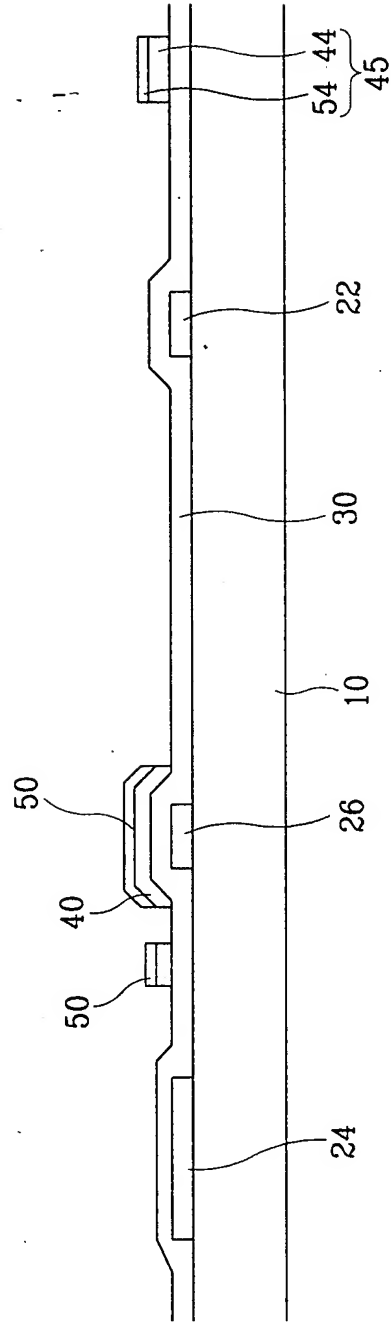


FIG. 10A

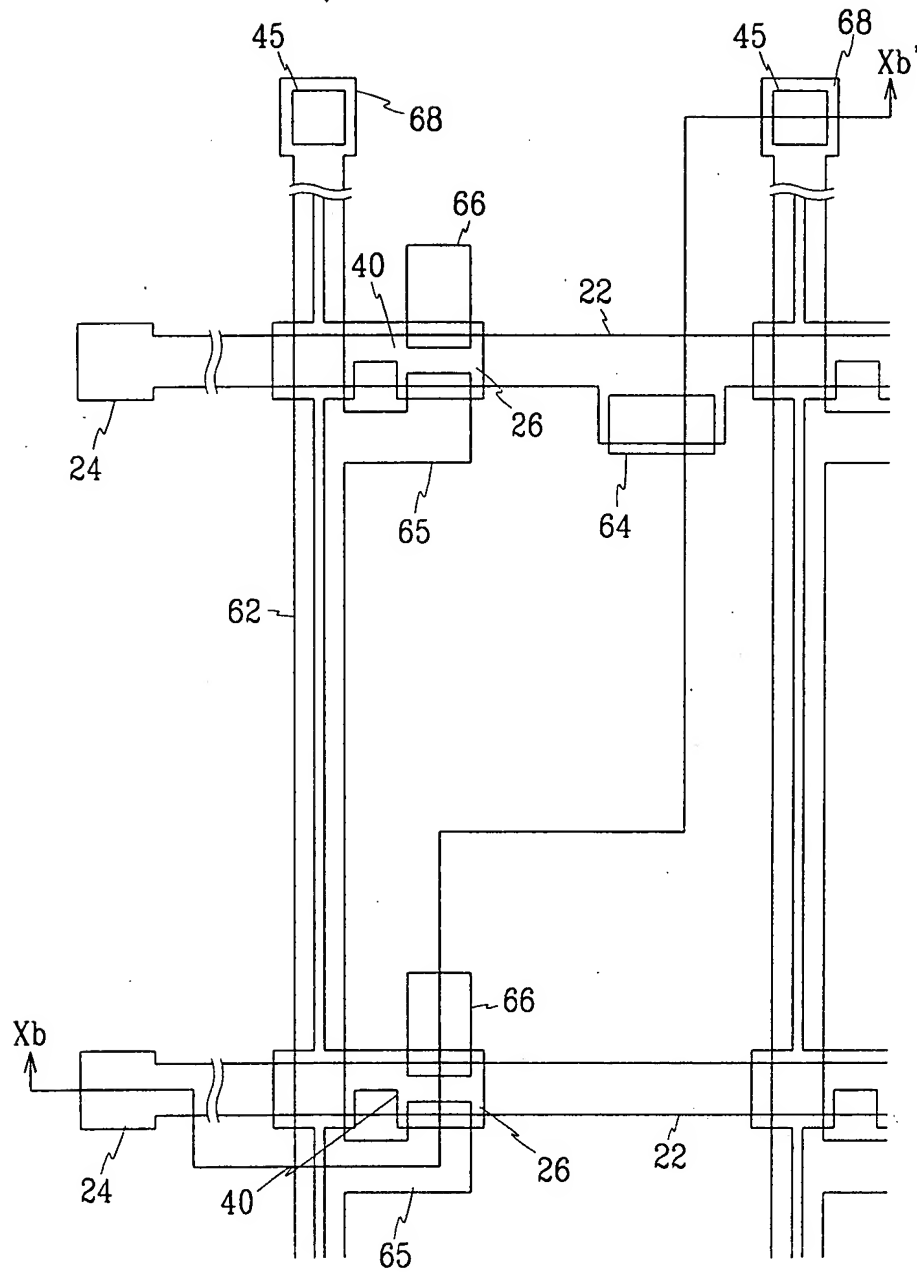


FIG. 10B

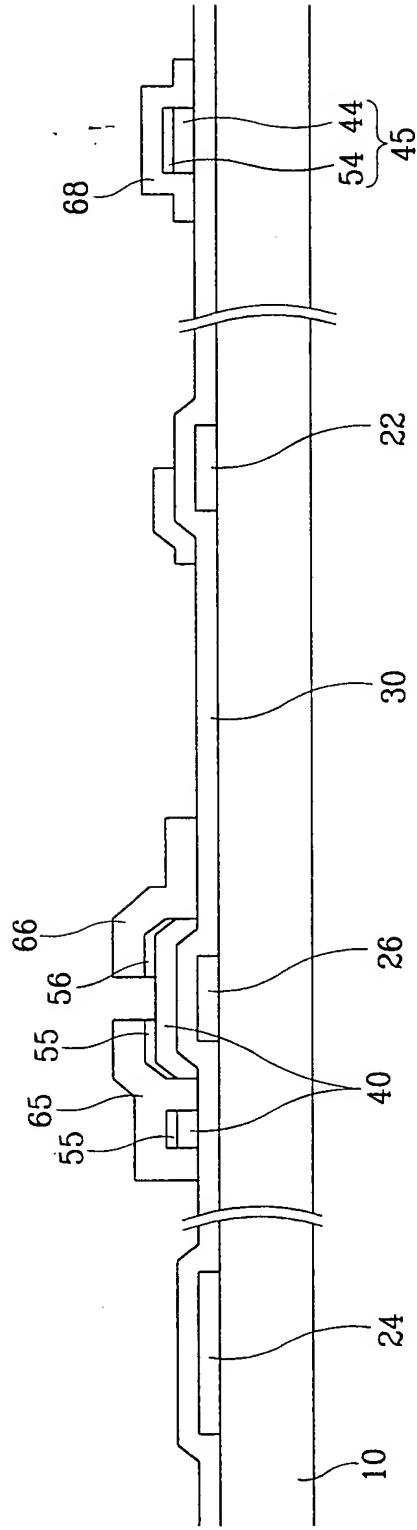
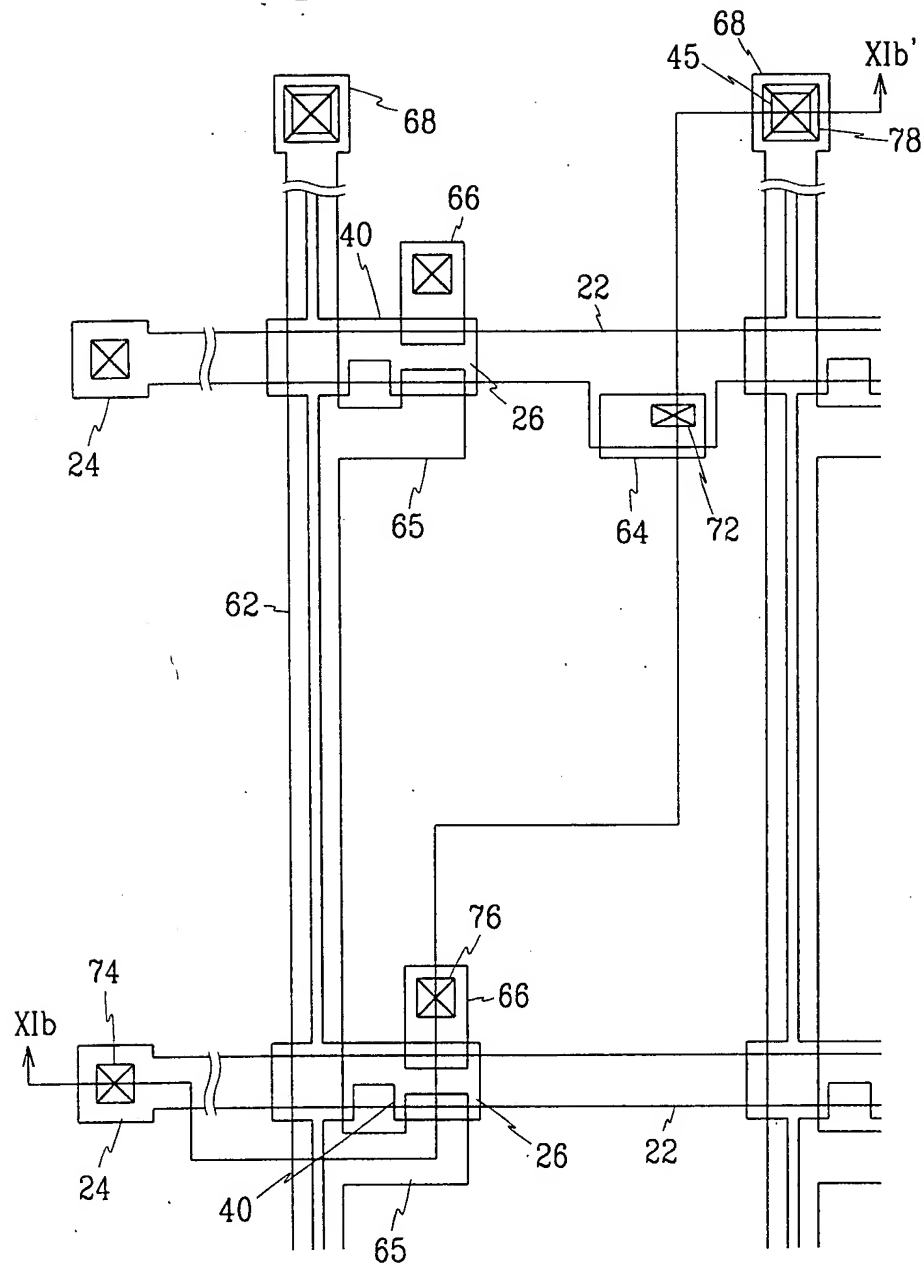


FIG. 11A



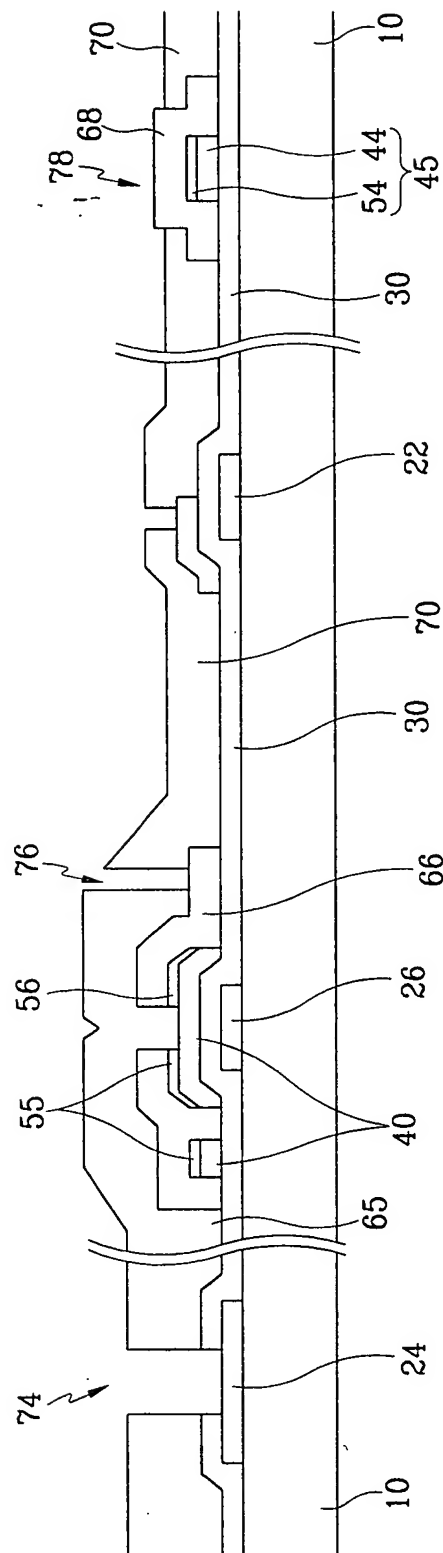


FIG. 12

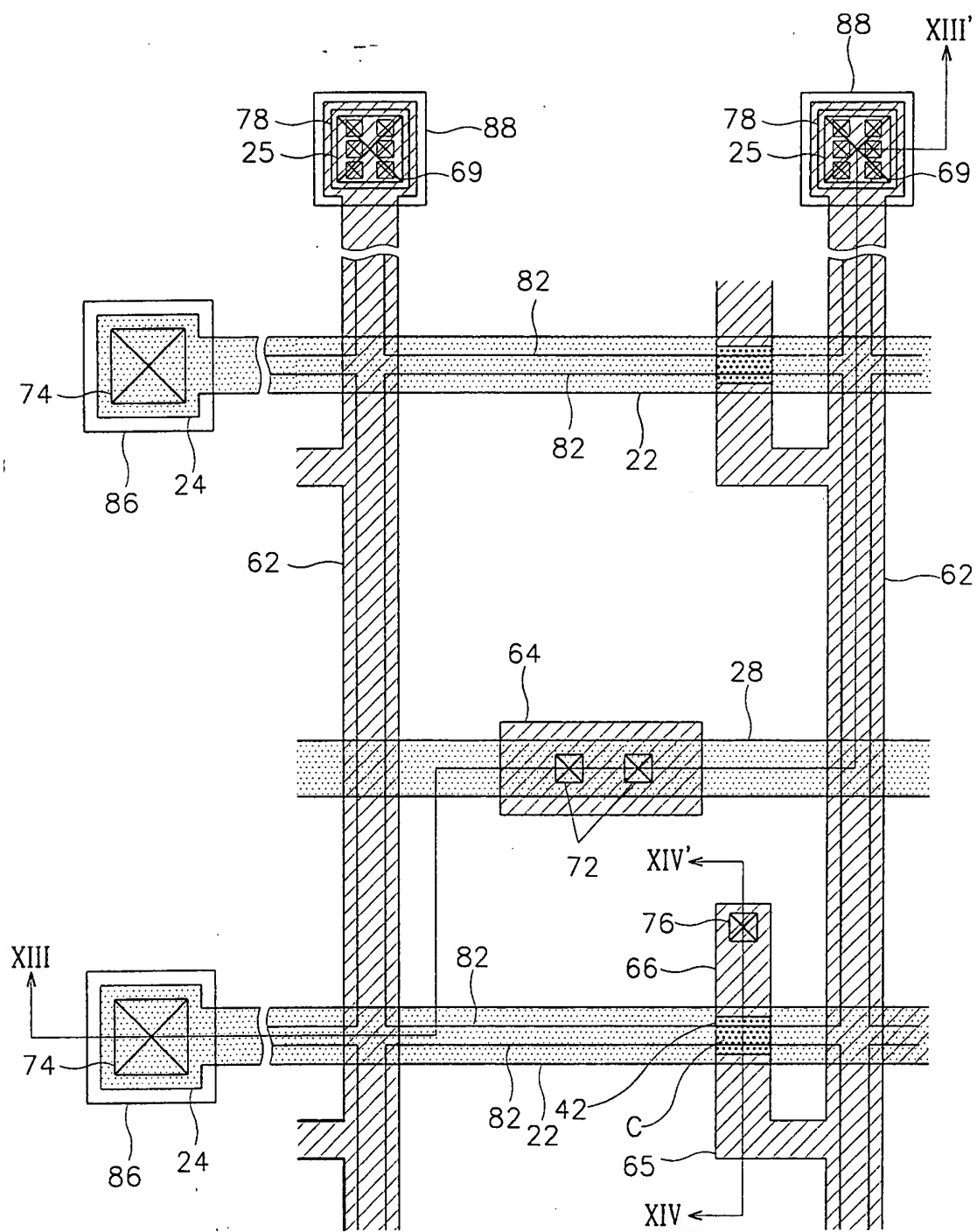
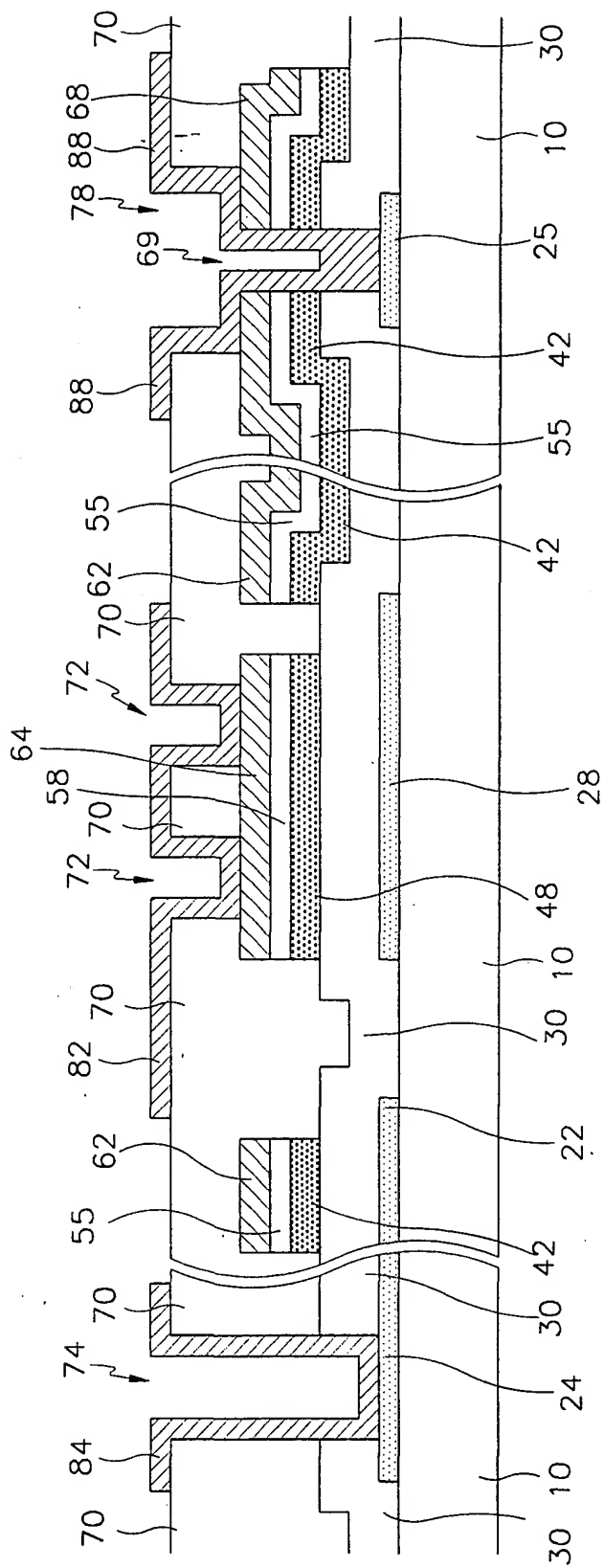


FIG. 13



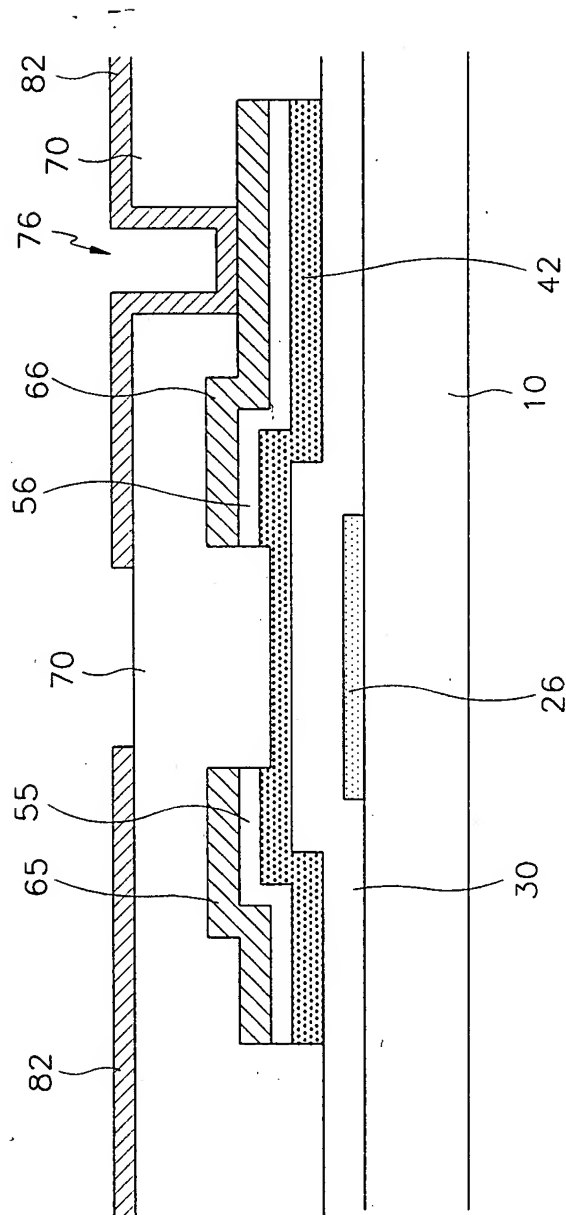


FIG. 15A

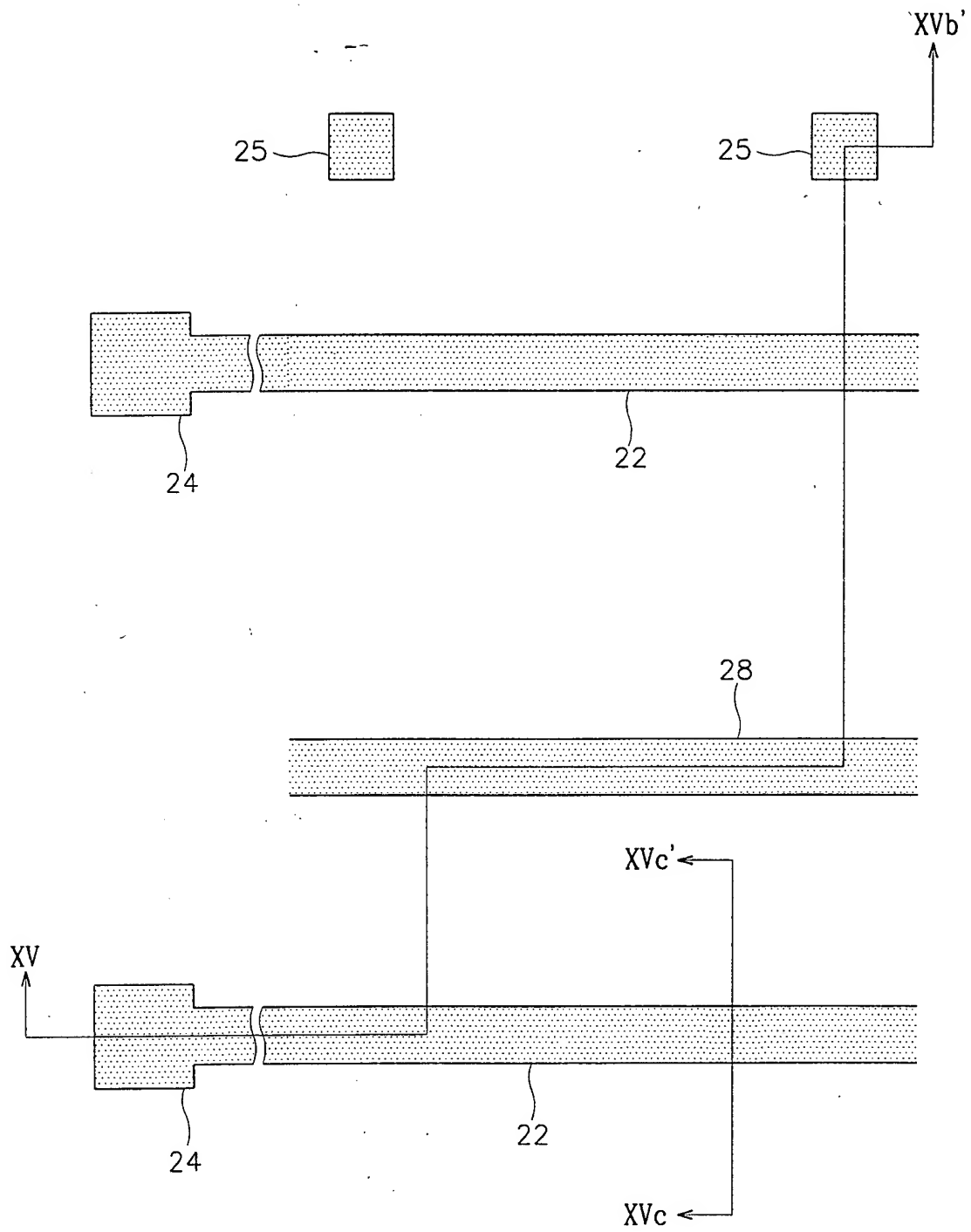


FIG. 15B

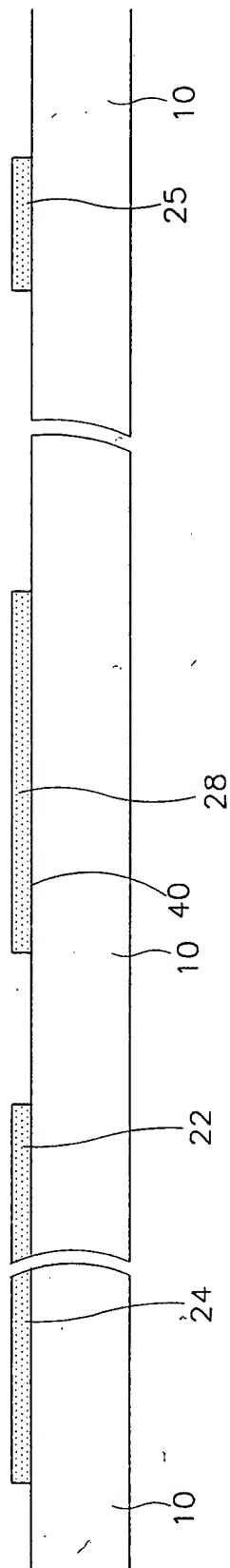


FIG. 15C

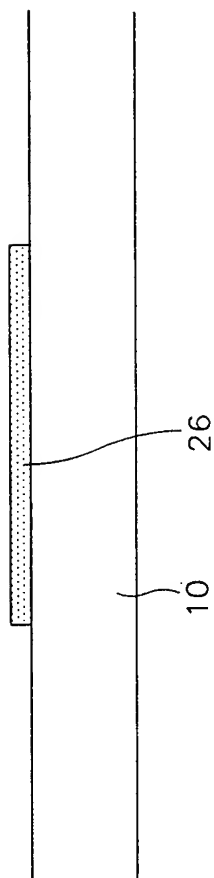


FIG. 16A

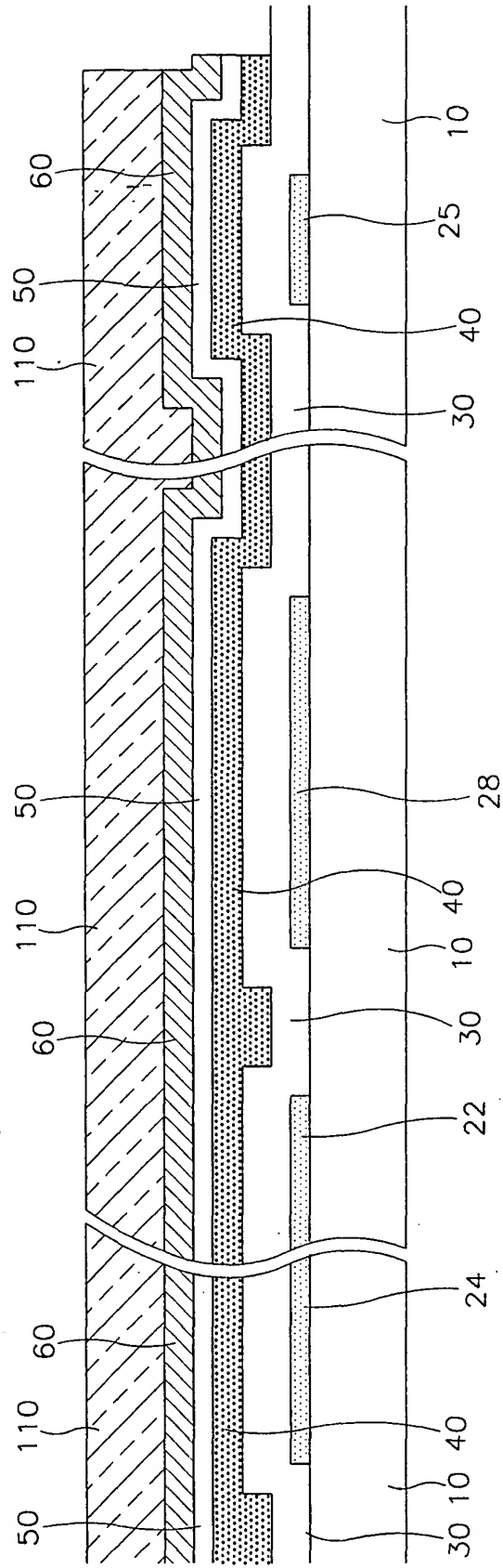


FIG. 16B

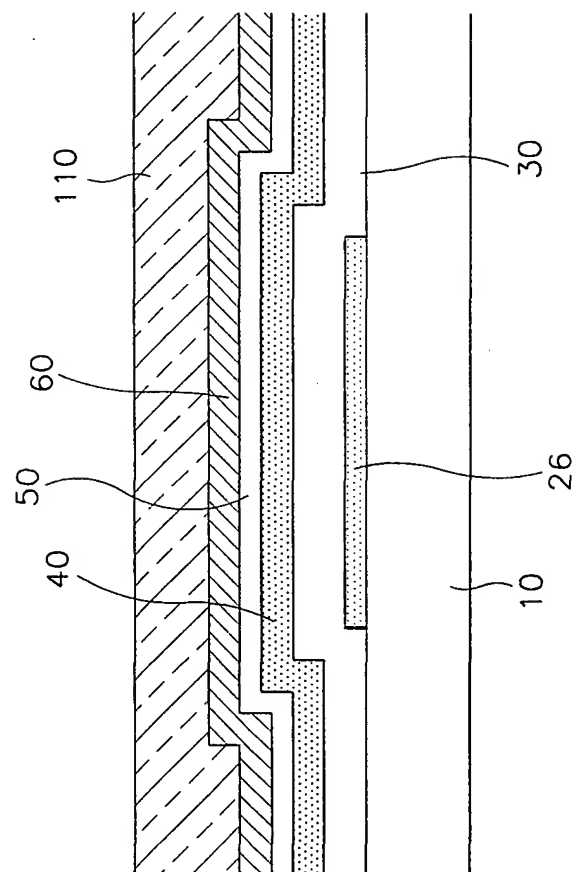
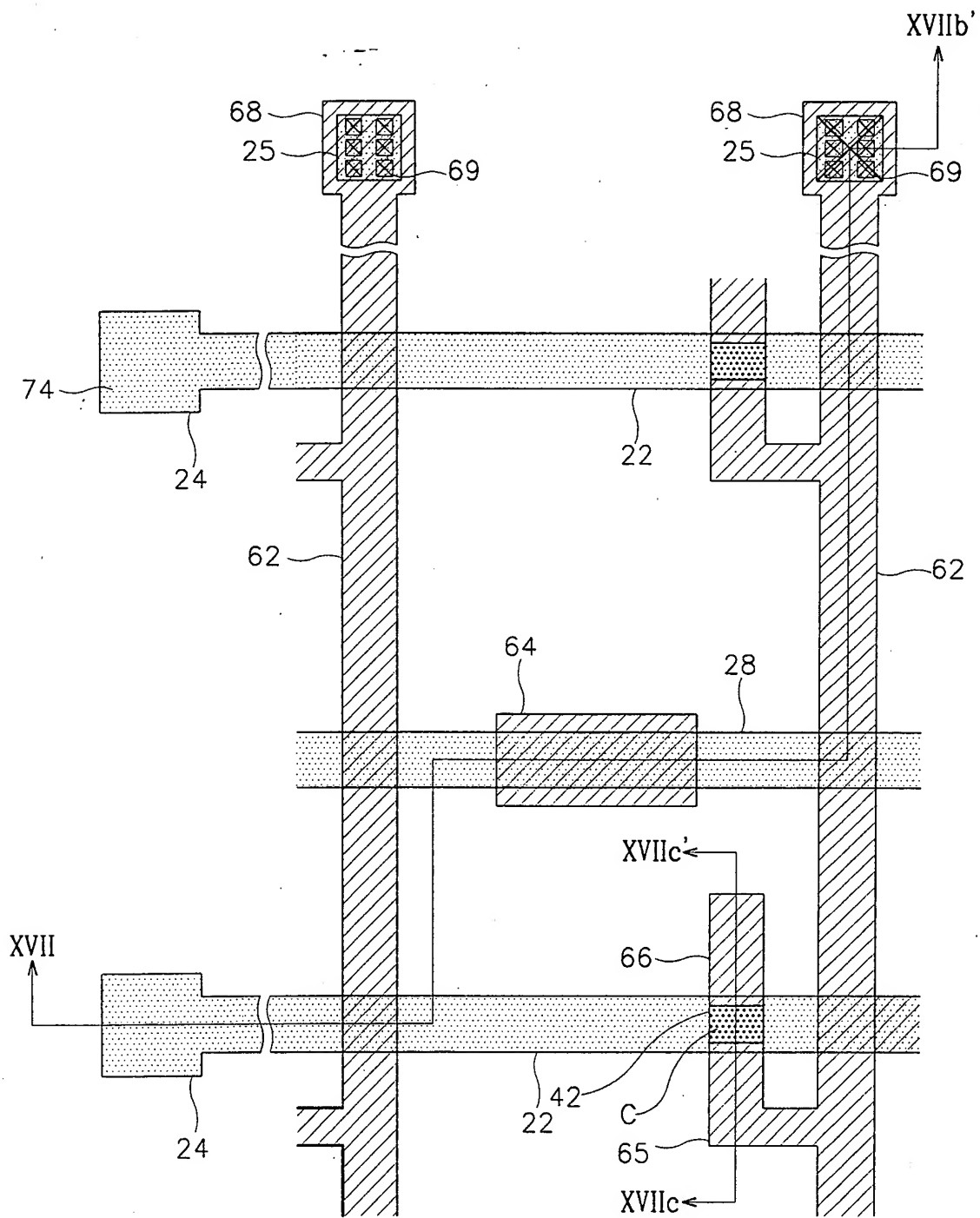


FIG. 17A



[illegible]

FIG. 17C

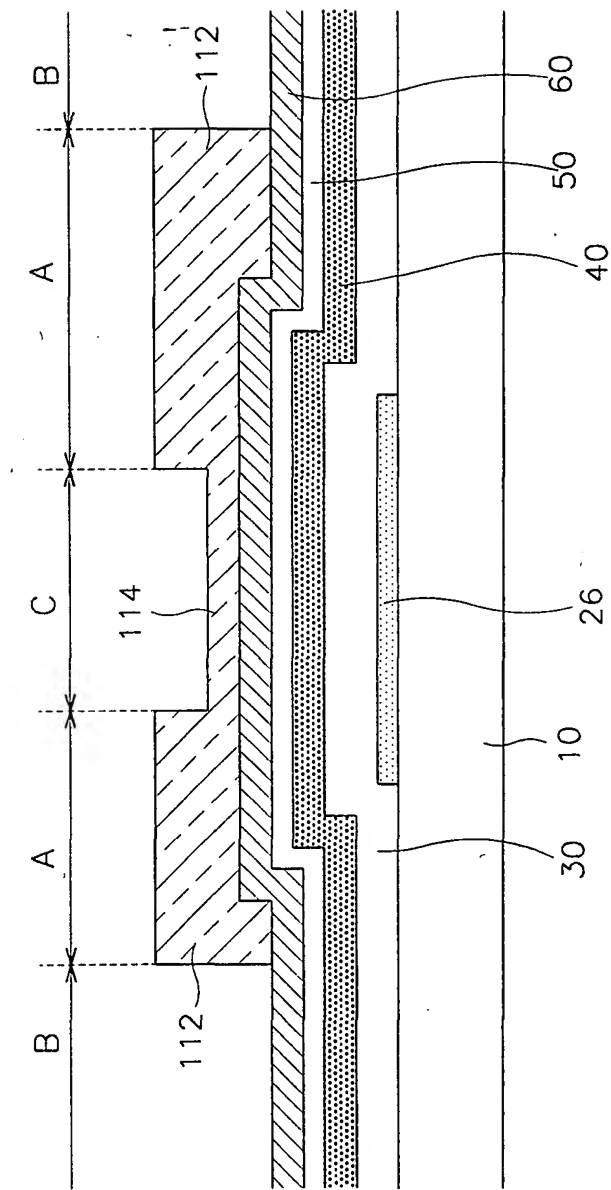
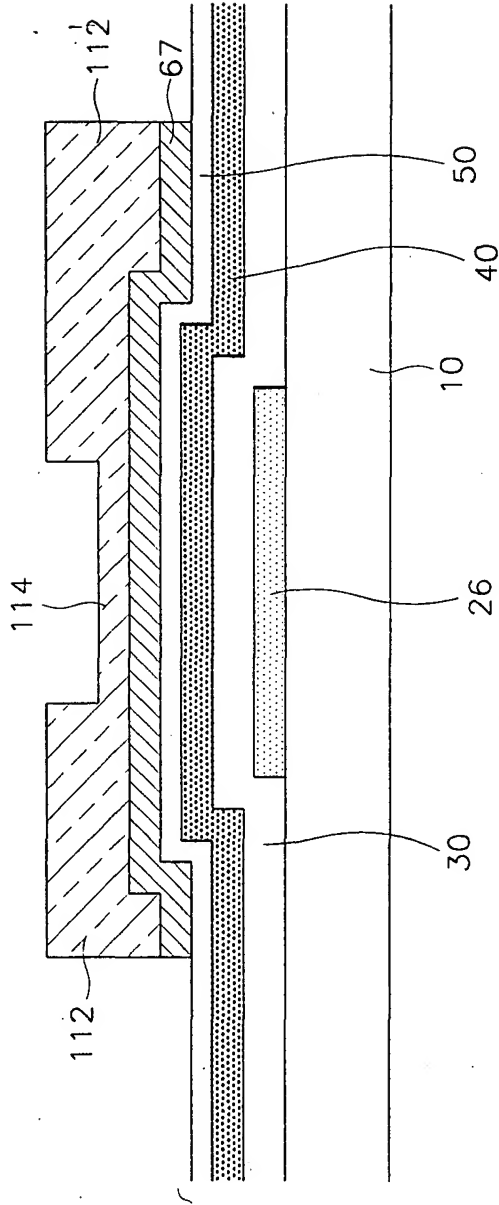


FIG. 18B



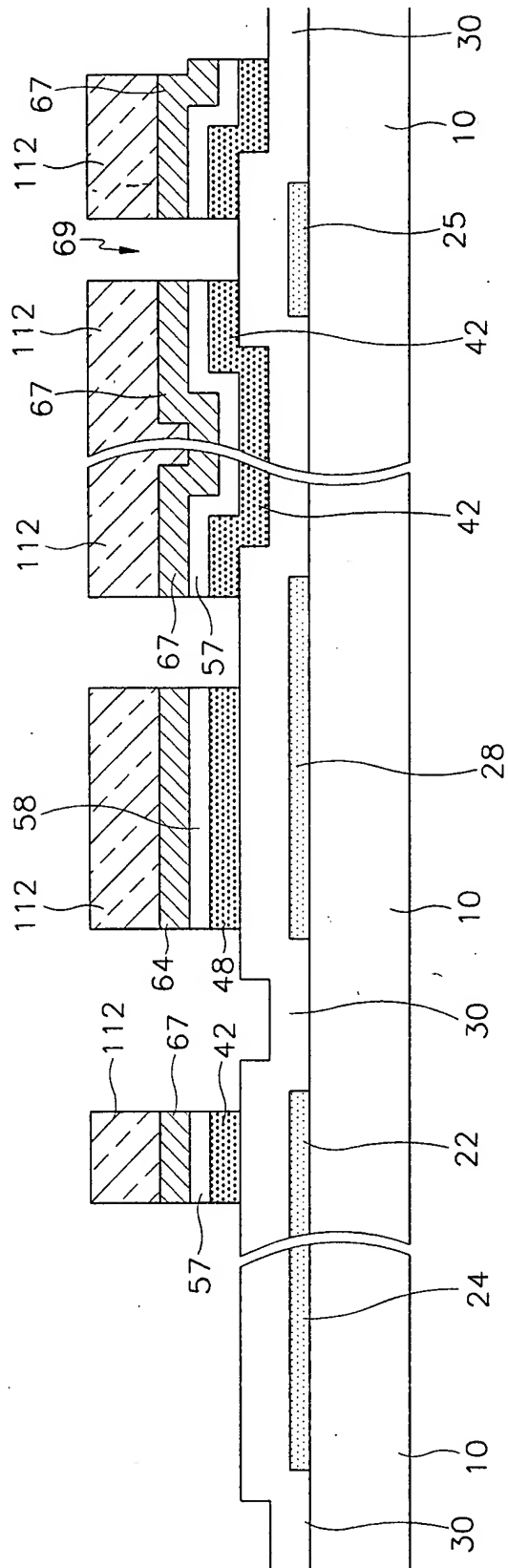
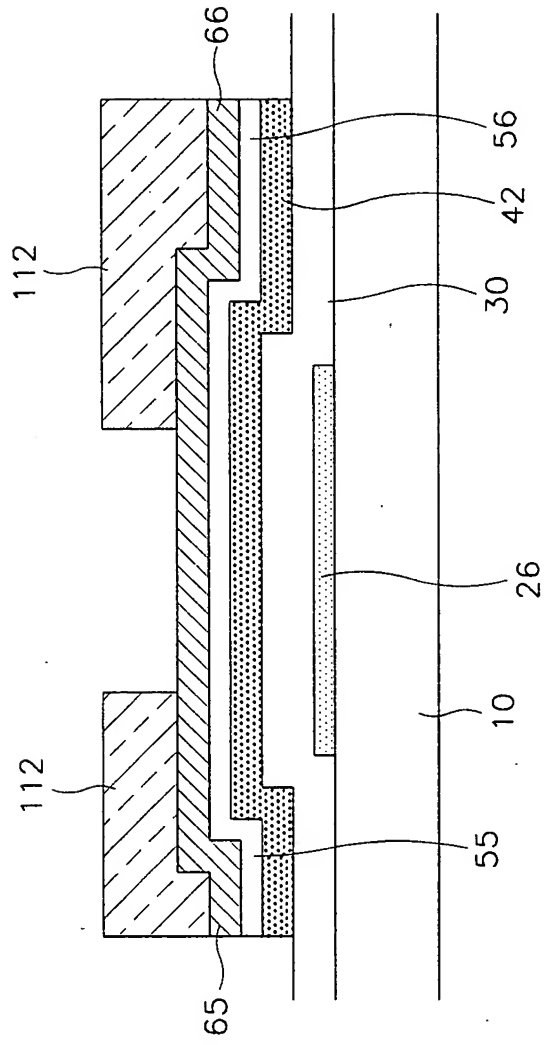
[illegible]

FIG. 19B



This cross-sectional view shows a central channel region (10) flanked by two side gate regions (112). The channel region contains a central layer (26) and is bounded by a layer (30). The side gate regions (112) are composed of a top layer (66) and a bottom layer (65). The device is situated on a substrate (55) with a top surface (56) and a bottom surface (42).

FIG. 21A

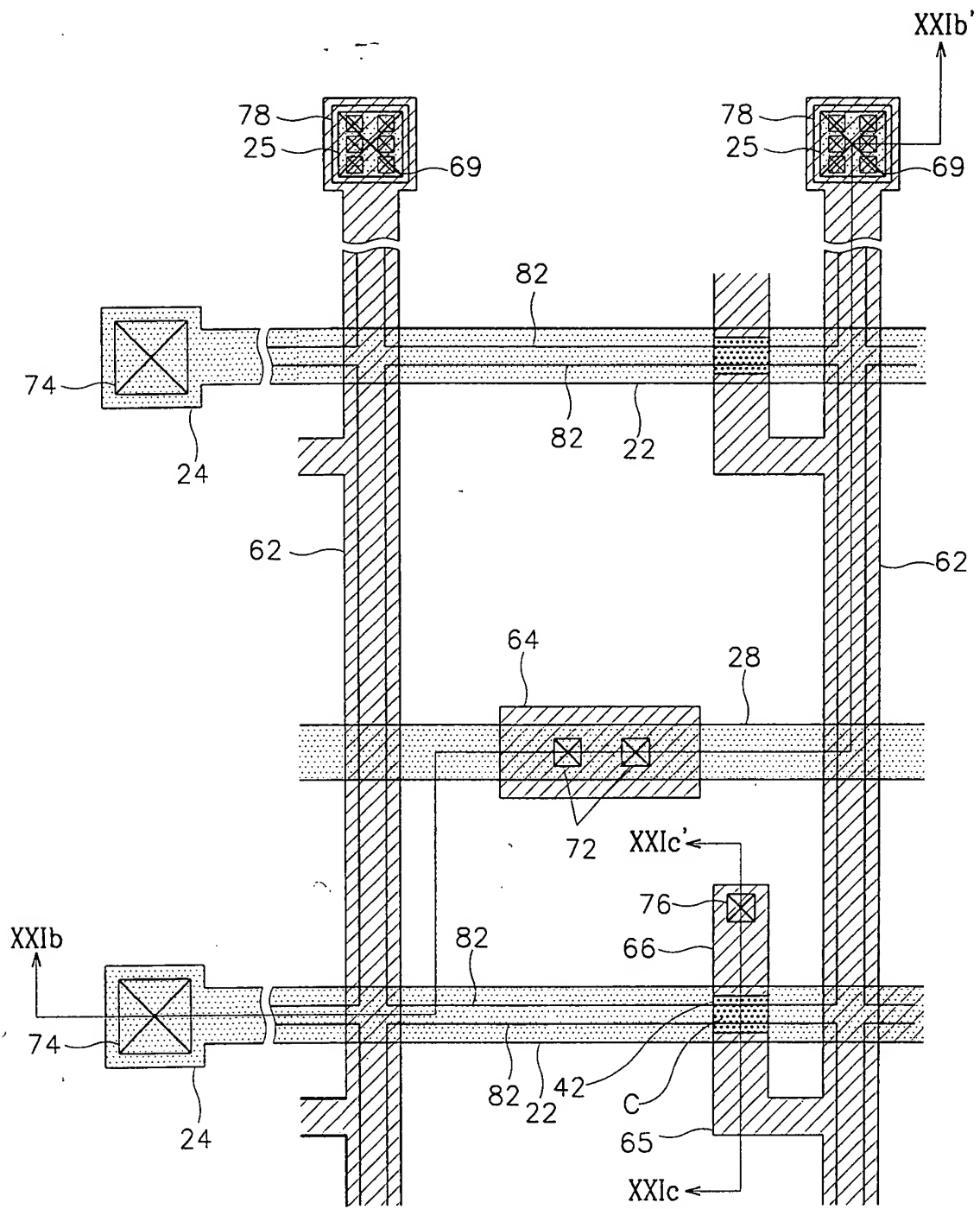


FIG. 21B

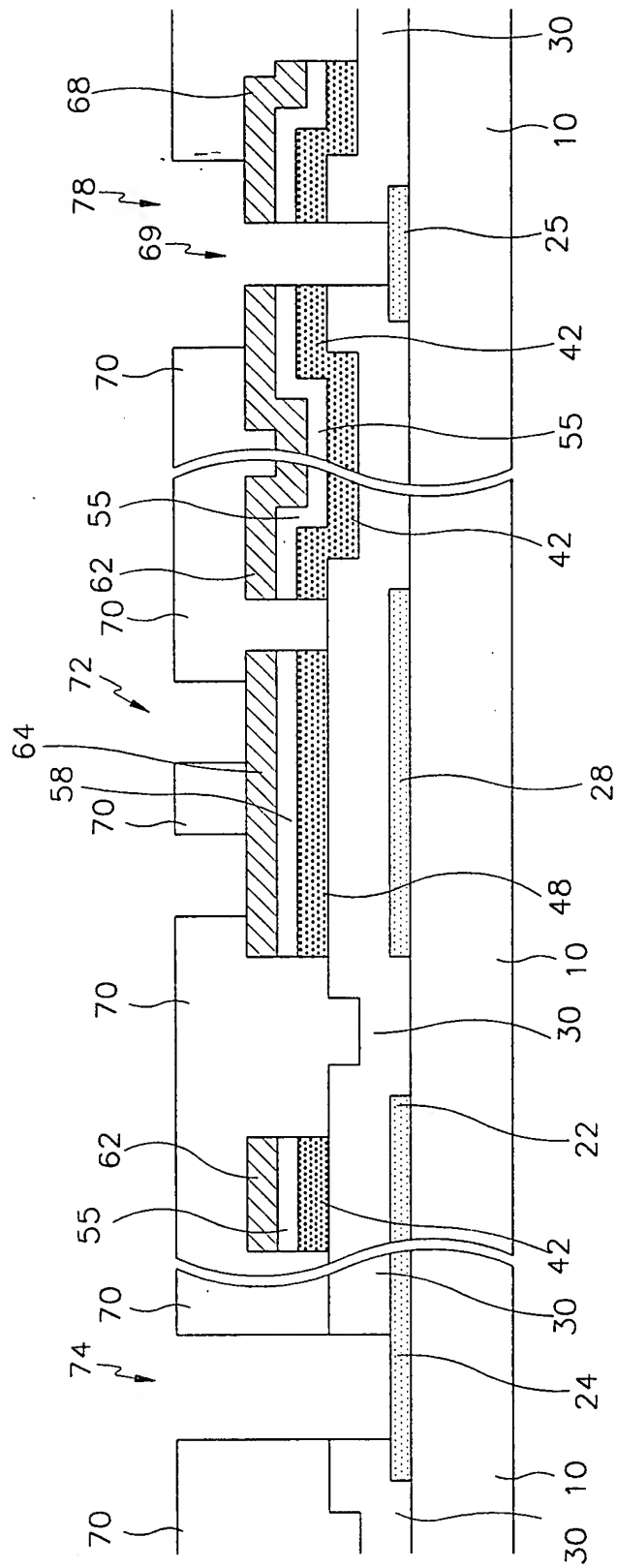


FIG. 21C

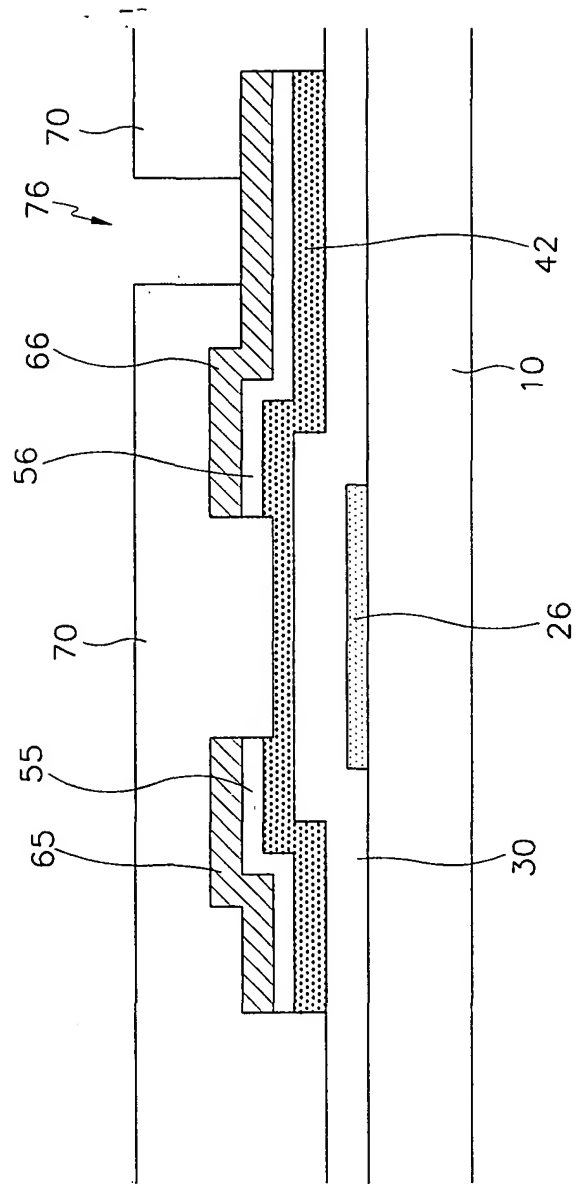


FIG. 22

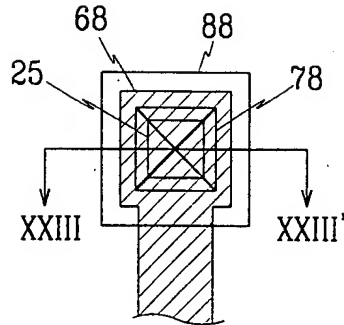


FIG. 23

